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Response Under 37 CFR 1.116  
Expedited Procedure  
Group No.: 2825  
2-403

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: M. FUNABASHI  
Application No.: 09/902,673  
Filed: July 12, 2001  
For: METHOD OF MANUFACTURING A SEMICONDUCTOR  
INTEGRATED CIRCUIT DEVICE  
Art Group: 2825  
Examiner: L. Malsawma

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AMENDMENT AFTER FINAL REJECTION

ATTN: BOX AF  
Commissioner for Patents  
Washington, D.C. 20231

January 29, 2003

Sir:

In response to the Office Action mailed July 29, 2002, the time period for responding having been extended until January 29, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 31 without prejudice or disclaimer, and add the following new claim to the application.

--33. A method of manufacturing a semiconductor integrated circuit device according to claim 20, wherein said processing solution etches the silicon oxide but does not etch the silicon wafer.--

Do not Enter